Darlington Power Transistors

DPAK For Surface Mount Applications

Designed for general purpose power and switching such as output or driver stages in applications such as switching regulators, convertors, and power amplifiers.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Monolithic Construction With Built-in Base-Emitter Shunt Resistors
- High DC Current Gain $h_{FE} = 2500$ (Typ) @ $I_C = 4.0$ Adc
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings:
 - Human Body Model, 3B > 8000 V
 - Machine Model, C > 400 V
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Pb-Free Package is Available*

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	80	Vdc
Collector-Base Voltage	V _{CB}	80	Vdc
Emitter-Base Voltage	V _{EB}	5	Vdc
Collector Current Continuous Peak	I _C	4 8	Adc
Base Current	Ι _Β	100	mAdc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	20 0.16	W W/°C
Total Power Dissipation (Note 1) @ T _A = 25°C Derate above 25°C	P _D	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



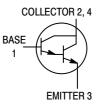
ON Semiconductor®

http://onsemi.com

SILICON POWER TRANSISTORS 4 AMPERES, 80 VOLTS, 20 WATTS



DPAK CASE 369C STYLE 1



MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week J6039 = Device Code G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MJD6039T4	DPAK	2,500/Tape & Reel
MJD6039T4G	DPAK (Pb-Free)	2,500/Tape & Reel
NJVMJD6039T4G	DPAK (Pb-Free)	2,500/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

These ratings are applicable when surface mounted on the minimum pad sizes recommended.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	71.4	°C/W

^{2.} These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				•
Collector–Emitter Sustaining Voltage (I _C = 30 mAdc, I _B = 0)	V _{CEO(sus)}	80	-	Vdc
Collector-Cutoff Current (V _{CE} = 40 Vdc, I _B = 0)	I _{CEO}	-	10	μAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain	h _{FE}	1000 500	- -	-
Collector–Emitter Saturation Voltage (I _C = 2 Adc, I _B = 8 mAdc)	V _{CE(sat)}	-	2.5	Vdc
Base-Emitter On Voltage (I _C = 2 Adc, V _{CE} = 4 Vdc)	V _{BE(on)}	-	2.8	Vdc
DYNAMIC CHARACTERISTICS	·			
Small-Signal Current Gain (I _C = 0.75 Adc, V _{CE} = 10 Vdc, f = 1 kHz)	h _{fe}	25	-	_
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz)	C _{ob}	-	100	pF

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

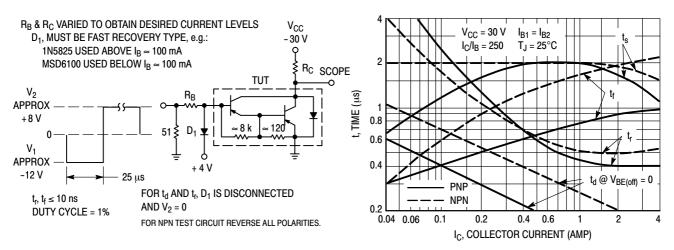


Figure 1. Switching Times Test Circuit

Figure 2. Switching Times

TYPICAL ELECTRICAL CHARACTERISTICS

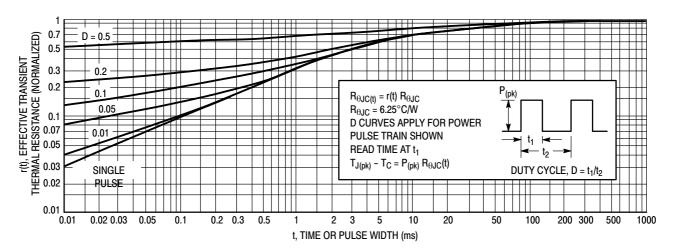


Figure 3. Thermal Response

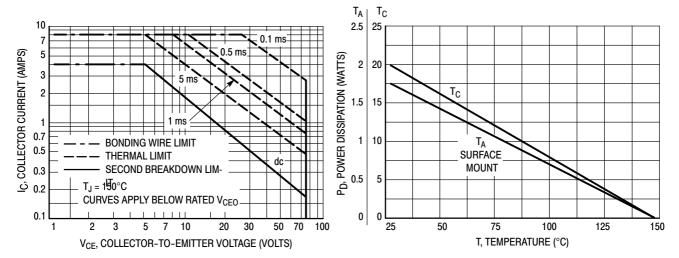


Figure 4. Maximum Rated Forward Biased Safe Operating Area

Figure 5. Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 6 and 7 is based on $T_{J(pk)} = 150^{\circ} C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 150^{\circ} C$. $T_{J(pk)}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

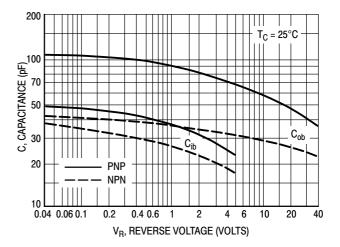


Figure 6. Capacitance

TYPICAL ELECTRICAL CHARACTERISTICS

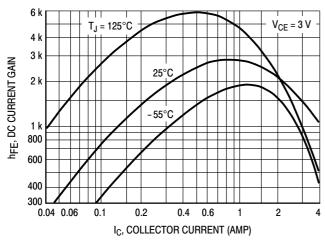


Figure 7. DC Current Gain

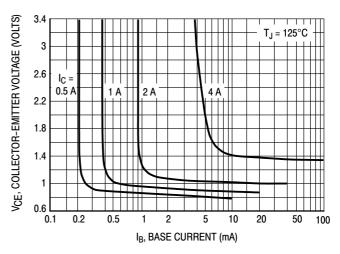


Figure 8. Collector Saturation Region

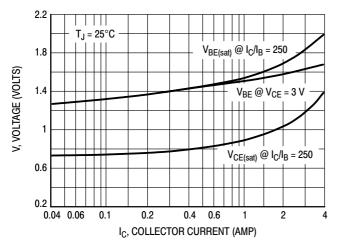


Figure 9. "On" Voltages

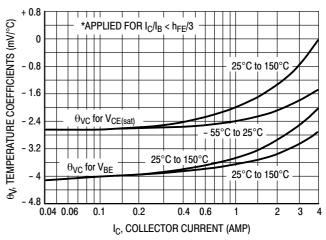


Figure 10. Temperature Coefficients

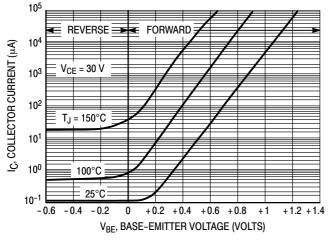


Figure 11. Collector Cut-Off Region

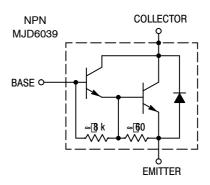
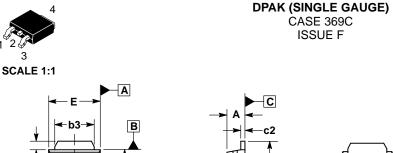
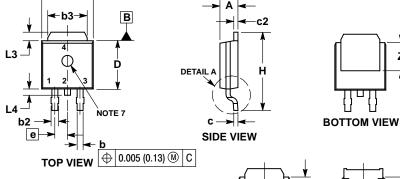
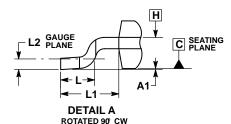


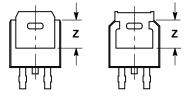
Figure 12. Darlington Schematic

DATE 21 JUL 2015





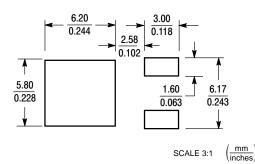




BOTTOM VIEW ALTERNATE CONSTRUCTIONS

STYLE 1: PIN 1. BASE 2. COLLE 3. EMITTI 4. COLLE	ER 3. SOL	AIN 2. CATI JRCE 3. ANO	HODE 2. ANODE DE 3. GATE	STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE
STYLE 6:	STYLE 7:	3. ANODE	STYLE 9:	STYLE 10:
PIN 1. MT1	PIN 1. GATE		PIN 1. ANODE	PIN 1. CATHODE
2. MT2	2. COLLECTOR		2. CATHODE	2. ANODE
3. GATE	3. EMITTER		3. RESISTOR ADJUST	3. CATHODE
4. MT2	4. COLLECTOR		4. CATHODE	4. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

z

- IOTES. 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: INCHES. 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-

- MENSIONS b3, L3 and Z.

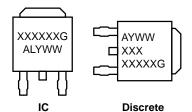
 Jimensions b And E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.

 MENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

 6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

		INCHES		MILLIM	IETERS
	DIM	MIN	MAX	MIN	MAX
	Α	0.086	0.094	2.18	2.38
	A1	0.000	0.005	0.00	0.13
	b	0.025	0.035	0.63	0.89
ĺ	b2	0.028	0.045	0.72	1.14
	b3	0.180	0.215	4.57	5.46
	С	0.018	0.024	0.46	0.61
	c2	0.018	0.024	0.46	0.61
	D	0.235	0.245	5.97	6.22
	Е	0.250	0.265	6.35	6.73
	е	0.090	BSC	2.29	BSC
	Н	0.370	0.410	9.40	10.41
	L	0.055	0.070	1.40	1.78
	L1	0.114	REF	2.90	REF
ĺ	L2	0.020	BSC	0.51	BSC
	L3	0.035	0.050	0.89	1.27
	L4		0.040		1.01
	Z	0.155		3.93	

GENERIC MARKING DIAGRAM*



XXXXXX = Device Code = Assembly Location Α L = Wafer Lot Υ = Year

WW = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.

DOCUMENT NUMBER:	98AON10527D	E
STATUS:	ON SEMICONDUCTOR STANDARD	a ve
NEW STANDARD:	REF TO JEDEC TO-252	"(
DESCRIPTION:	DPAK SINGLE GAUGE SURFACE MOU	NT

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PAGE 1 OF 2



DOCUMENT	NUMBER:
98AON10527	7D

PAGE 2 OF 2

ISSUE	REVISION	DATE
0	RELEASED FOR PRODUCTION. REQ. BY L. GAN	24 SEP 2001
Α	ADDED STYLE 8. REQ. BY S. ALLEN.	06 AUG 2008
В	ADDED STYLE 9. REQ. BY D. WARNER.	16 JAN 2009
С	ADDED STYLE 10. REQ. BY S. ALLEN.	09 JUN 2009
D	RELABELED DRAWING TO JEDEC STANDARDS. ADDED SIDE VIEW DETAIL A. CORRECTED MARKING INFORMATION. REQ. BY D. TRUHITTE.	29 JUN 2010
E	ADDED ALTERNATE CONSTRUCTION BOTTOM VIEW. MODIFIED DIMENSIONS b2 AND L1. CORRECTED MARKING DIAGRAM FOR DISCRETE. REQ. BY I. CAMBALIZA.	06 FEB 2014
F	ADDED SECOND ALTERNATE CONSTRUCTION BOTTOM VIEW. REQ. BY K. MUSTAFA.	21 JUL 2015

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